

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

_____ forming a film to be patterned;
_____ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and
_____ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,

_____ wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).

3. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

_____ forming a film to be patterned;
_____ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and
_____ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,

_____ wherein said top resist pattern is made of a resist material with phenol-based hydroxide.

4. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

forming a film to be patterned;
forming, on said film, a laminated resist pattern with a T-shaped cross section
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top
resist pattern being larger than a surface area of said bottom resist pattern; and
increasing a width of said top resist pattern after said film is patterned via said
laminated resist pattern,
_____ wherein said surface area of said top resist pattern is increased by coating a
water-soluble resin at least over said top resist pattern of said laminated resist pattern.

5. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

6. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

7. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

forming a film to be patterned;
forming, on said film, a laminated resist pattern with a T-shaped cross section
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top
resist pattern being larger than a surface area of said bottom resist pattern; and
increasing a width of said top resist pattern after said film is patterned via said
laminated resist pattern,
_____ wherein said laminated resist pattern is not removed through the fabrication
process of patterned thin film.

8. (Currently Amended) ~~The fabricating method as defined in claim 1,~~ A method for fabricating a mask, comprising:

_____ forming a film to be patterned;
_____ forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and
_____ increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,
_____ wherein said film is patterned via said laminated resist pattern by means of dry etching.

9. (Canceled)

10. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

_____ forming a first thin film to be patterned;
_____ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;
_____ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;
_____ increasing a width of said top resist pattern; and
_____ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,
_____ wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).

11. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

forming a first thin film to be patterned;
forming, on said first thin film, a laminated resist pattern with a T-shaped
cross section and composed of a bottom resist pattern and a top resist pattern, a surface area
of said top resist pattern being larger than a surface area of said bottom resist pattern;
patterning said first thin film via said laminated resist pattern, to form a first
patterned thin film;
increasing a width of said top resist pattern; and
forming a second patterned thin film along a contour of said top resist pattern
of said laminated resist pattern,
_____ wherein said top resist pattern is made of a resist material with phenol-based
hydroxide.

12. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method
for fabricating a patterned thin film, comprising:

_____ forming a first thin film to be patterned;
_____ forming, on said first thin film, a laminated resist pattern with a T-shaped
cross section and composed of a bottom resist pattern and a top resist pattern, a surface area
of said top resist pattern being larger than a surface area of said bottom resist pattern;
_____ patterning said first thin film via said laminated resist pattern, to form a first
patterned thin film;
_____ increasing a width of said top resist pattern; and
_____ forming a second patterned thin film along a contour of said top resist pattern
of said laminated resist pattern,
_____ wherein said surface area of said top resist pattern is increased by coating a
water-soluble resin at least over said top resist pattern of said laminated resist pattern.

13. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

14. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

15. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

_____ forming a first thin film to be patterned;

_____ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

_____ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

_____ increasing a width of said top resist pattern; and

_____ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

_____ wherein said laminated resist pattern is not removed through the fabrication process of said first patterned thin film and said second patterned thin film.

16. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

_____ forming a first thin film to be patterned;

_____ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

_____ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

_____ increasing a width of said top resist pattern; and

_____ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

_____ wherein said film is patterned via said laminated resist pattern by means of dry etching.

17. (Currently Amended) ~~The fabricating method as defined in claim 9,~~ A method for fabricating a patterned thin film, comprising:

_____ forming a first thin film to be patterned;

_____ forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

_____ patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

_____ increasing a width of said top resist pattern; and

_____ forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

_____ wherein said second patterned thin film is located away from said first patterned thin film by a minute gap.

18. (Original) The fabricating method as defined in claim 17, wherein said second patterned thin film is composed of a pair of patterned thin films, which are located at both sides of said first patterned thin film by minute gaps.

19-22. (Canceled)